# intersi

# ACS138MS

Radiation Hardened 3-to-8 Line Decoder/Demultiplexer

## Features

- QML Qualified Per MIL-PRF-38535 Requirements
- 1.25Micron Radiation Hardened SOS CMOS
- Radiation Environment
  - Latch-up Free Under any Conditions
- Input Logic Levels ... VIL = (0.3V)(V<sub>CC</sub>), VIH = (0.7V)(V<sub>CC</sub>)
- Output Current ......±12mA
- Propagation Delay ......15ns

# Applications

- · Memory Decoding
- Data Routing
- Code Conversion

## Ordering Information

# Description

The Radiation Hardened ACS138MS is an Inverting 3-to-8 Line Decoder/Demultiplexer with three binary select inputs (A0, A1 and A2). If the device is enabled, these inputs determine which one of the eight normally high outputs will go low.

Two active low and one active high enable inputs ( $\overline{E}_1$ ,  $\overline{E}_2$ ) and E<sub>3</sub>) are provided to make cascaded decoder designs easier to implement.

The ACS138MS is fabricated on a CMOS Silicon on Sapphire (SOS) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment. These devices offer significant power reduction and faster performance when compared to ALSTTL types.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the ACS138 are contained in SMD 5962-98534.

SMD PART NUMBER	INTERSIL PART NUMBER	TEMP. RANGE ( <sup>O</sup> C)	PACKAGE	CASE OUTLINE
5962F9853401VEC	ACS138DMSR-02	-55 to 125	16 Ld SBDIP	CDIP2-T16
N/A	ACS138D/Sample-02	25	16 Ld SBDIP	CDIP2-T16
5962F9853401VXC	ACS138KMSR-02	-55 to 125	16 Ld Flatpack	CDFP4-F16
N/A	ACS138K/Sample-02	25	16 Ld Flatpack	CDFP4-F16
N/A	ACS138HMSR-02	25	Die	N/A

## **Pinouts**









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## **Die Characteristics**

### DIE DIMENSIONS:

Size:  $2390\mu m \times 2390\mu m$  (94 mils x 94 mils) Thickness:  $525\mu m \pm 25\mu m$  (20.6 mils  $\pm 1$  mil) Bond Pad:  $110\mu m \times 110\mu m$  (4.3 x 4.3 mils)

#### METALLIZATION: AI

Metal 1 Thickness:  $0.7\mu m \pm 0.1\mu m$ Metal 2 Thickness:  $1.0\mu m \pm 0.1\mu m$ 

#### SUBSTRATE POTENTIAL:

Unbiased Insulator

# Metallization Mask Layout

#### PASSIVATION

Type: Phosphorous Silicon Glass (PSG) Thickness:  $1.30 \mu m \pm 0.15 \mu m$ 

#### SPECIAL INSTRUCTIONS:

Bond V<sub>CC</sub> First

#### ADDITIONAL INFORMATION:

Worst Case Density: <2.0 x 10<sup>5</sup> A/cm<sup>2</sup> Transistor Count: 220



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